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INFORMATION DISCLOSURE STATEMENT

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Applicant: Hisashi OHTANI et al.

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U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
EP	3,791,883	02/12/74	TAKEI et al.	140	—	
EP	4,502,204	03/05/85	TOGASHI et al.	29	—	
EP	4,851,363	07/25/89	TROXELL et al.	437	—	
EP	5,108,843	04/28/92	OHTAKA et al.	428	—	
EP	5,289,030	02/22/94	YAMAZAKI et al.	257	—	

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation Yes No	
EP	56-24925	03/10/81	Japan	—	—	abstract	
EP	6-13610	01/21/94	Japan	—	—	abstract	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EP	Y. Kawazu et al, Jpn. J. Appl Phys, 29, 12 (1990) pp. 2698-2704 "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation"
EP	T. Sato et al., Physical Review B, Vo. 4, No. 6, 1971, pp.1950-1960 "Mobility Anisotropy of Electrons in Inversion Layers on Oxidized Silicon Surfaces"

Examiner:

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Date Considered:

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*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.